

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a semiconductor circuit which is formed inside; and an electrode structure which is formed on a first surface thereof. The electrode structure has a first electrode layer and a metal plating layer. The first electrode layer is formed of a first metal and is connected to the semiconductor circuit. The metal plating layer is formed of a second metal on the first electrode layer. The second metal is capable of being soldered on an extraction electrode outside of the semiconductor device.